

This diagram shows a cross-section of a semiconductor device 30. The substrate 32 consists of several layers: 34, 36, 38, 42, 46, and 50. Two vertical structures 48 are formed, each with a top layer 52 and 55. A central trench 53 is located between them. A gate layer 57 is on the surface. The device is shown in a cross-sectional view with various layers and structures labeled with reference numerals.

FIGURE 2

